

ABSTRACT OF THE DISCLOSURE

In a process for the fabrication of integrated resistive elements with protection from silicidation, at least one active area (15) is delimited in a semiconductor wafer (10). At least one resistive region (21) having a pre-determined resistivity is then formed in the active area (15). Prior to forming the resistive region (21), however, a delimitation structure (20) for delimiting the resistive region (21) is obtained on top of the active area (15). Subsequently, protective elements (25) are obtained which extend within the delimitation structure (20) and coat the resistive region (21).